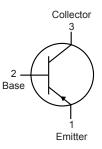
# **Bipolar Transistor**











### **Description:**

Silicon TO-126, PNP Power Transistor for use in power amplifier and switching excellent safe area limits

#### **Maximum Ratings:**

Characteristic	Symbol	Rating	Unit	
Collector-Base Voltage	V <sub>CBO</sub>	80		
Collector-Emitter Voltage	V <sub>CEO</sub>	00	V	
Emitter-Base Voltage	V <sub>EBO</sub>	5		
Continuous Collector Current	I <sub>C</sub>	4	۸	
Base Current	I <sub>B</sub>	1	Α	
Total Device Dissipation (T <sub>C</sub> = +25°C) Derate Above 25°C	P <sub>D</sub>	40 320	W mW/°C	
Operating Junction Temperature Range	T <sub>J</sub>	05 to 1450	°C	
Storage Temperature Range	T <sub>stg</sub>	-65 to +150		

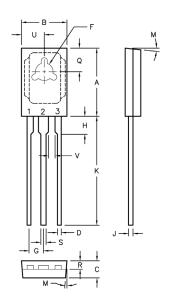


## **Bipolar Transistor**



Parameter	Symbol	Test Conditions	Min.	Max.	Unit
OFF Characteristics					
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	$I_{\rm C}$ = 100mA, $I_{\rm B}$ = 0 (Note 1)	80	-	V
	I <sub>CEO</sub>	$V_{CE} = 80V, I_{E} = 0$		1	
Collector Cut-Off Current	I <sub>CEX</sub>	$V_{CE} = 80V_{EB(off)}$ , $I_{E} = 1.5V$		0.1	mA
	I <sub>CBO</sub>	$V_{CB} = 80V, I_{E} = 0$ $V_{EB} = 5V, I_{C} = 0$		0.1	
Emitter Cut-Off Current	I <sub>EBO</sub>			1	
ON Characteristics					
DC Current Gain (Note 1)	h	$V_{CE} = 2V, I_{C} = 1.5A$	20	80	
	h <sub>FE</sub>	$V_{CE} = 2V$ , $I_{C} = 4A$	7	-	ı
Collector - Emitter Saturation Voltage (Note 1)	\/	$I_{\rm C} = 1.5 \text{A}, I_{\rm B} = .15 \text{mA}$		0.6	
	V <sub>CE(sat)</sub>	$I_{C} = 4A, I_{B} = 1A$	_	1.4	V
Base - Emitter on Voltage (Note 1)	$V_{BE(on)}$	$I_{\rm C}$ = 1.5A, $V_{\rm CE}$ = 2V		1.2	
Small Signal Characteristics					
Current Gain-Bandwidth Product	f <sub>⊤</sub>	$V_{CE} = 10V$ , $I_{C} = 1A$ , $f = 1MHz$	2	-	MHz

Note 1 : Pulse Test : Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%



Dimensions	Min.	Max.	
Α	10.8	11.05	
В	7.49	7.75	
С	2.41	2.67	
D	0.51	0.66	
F	2.92	3.18	
G	2.31	2.46	
Н	1.27	2.41	
J	0.38	0.64	
K	15.11	16.64	
М	3° TYP		
Q	3.76	4.01	
R	1.14	1.4	
S	0.64	0.89	
U	3.68	3.94	
V	1.02	-	

Dimensions: Millimetres

#### **Part Number Table**

Description	Part Number		
Transistor, PNP, 4A, 80V, TO-126	2N5195		

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